What is claimed is:

1. A method comprising:

forming at least one opening through a build up structure and a photo sensitive material disposed on the build up structure, wherein the build up structure comprises a portion of a package substrate;

filling the at least one opening with a metal containing nanopaste; and

sintering the metal containing nanopaste to form a bulk property metal structure in the at least one opening.

2. The method of claim 1 further comprising wherein the at least one opening comprises at least one fine conductive line opening comprising a width of less than about 10 microns and a space between adjacent fine conductive line openings of less than about 10 microns.

3. The method of claim 1 further comprising wherein the at least one opening comprises at least one via contact opening.

4. The method of claim 1 further comprising wherein the at least one opening is formed by utilizing at least one of nano imprinting and laser ablation.

5. The method of claim 1 wherein the bulk property metal structure comprises at least one of a metal contact via structure and a metal wire structure.

6. The method of claim 1 further comprising wherein a sintering temperature comprises less than about 280 degrees Celsius for less than about 60 minutes.

7. A method comprising:

forming at least one opening through a photo sensitive material and a build up structure, wherein the photosensitive material is disposed on the build up structure, and wherein the build up structure comprises a portion of a package substrate, and wherein the at least one opening comprises a width of less than about 10 microns and a space of less than about 10 microns between adjacent openings;

filling the at least one opening with a metal containing nanopaste; and

sintering the metal containing nanopaste to form a bulk property metal structure in the at least one opening.

8. The method of claim 7 further comprising wherein the package substrate comprises at least one of a high density package substrate and a motherboard.

9. The method of claim 7 further comprising wherein the metal containing nanopaste comprises nano-sized metal particles, dispersants, reaction rate control agents, and additives.

10. The method of claim 9 further comprising wherein the metal containing nanopaste comprises copper nanoparticles comprising a diameter of about 6 nm or less, and wherein the dispersants comprise at least one of alkanoic acid and amine compounds, and wherein the reaction rate control agents comprise an amine compound, and wherein the additives comprise solvents.

11. The method of claim 7 further comprising wherein a sintering temperature comprises less than about 280 degrees Celsius for about 60 minutes or less.

12. The method of claim 11 further comprising wherein the sintering temperature of the metal containing nanopaste comprises a lower temperature than a melting temperature of the bulk property metal structure.

13. The method of claim 9 further comprising wherein the sintering substantially removes the dispersants, reaction rate control agents, and additives from the metal containing nanopaste, and wherein the metal nanoparticles are transformed into a bulk property metal structure.

14. The method of claim 7 further comprising wherein filling the at least one opening with a metal containing nanopaste comprises at least one of squeezing and screen printing.

15. The method of claim 7 further comprising wherein a hydrophobic material is applied to the photosensitive material prior to filling the at least one opening.

16. The method of claim 7 further comprising wherein the at least one opening is formed with laser ablation.

17. The method of claim 7 further comprising wherein the bulk property metal structure comprises a metal wire structure with a line with of about 10 microns or less and a line spacing of about 10 microns or less.

18. A structure comprising:

a first conductive wire structure disposed in a build up material, wherein the build up material comprises a portion of a package substrate;

a second conductive wire structure disposed adjacent to the first conductive wire structure, wherein the first and second conductive wire structures comprise a width of less than about 10 microns and a spacing between the first and second conductive wire structures of less than about 10 microns.

19. The structure of claim 18 further comprising wherein the first and second conductive wire structures comprise a metal comprising bulk metal properties.

20. The structure of claim 18 further comprising wherein the first and second conductive wire structures comprise a metallic wire structure.

21. The structure of claim 18 further comprising wherein the package substrate comprises at least one of a high density package substrate and a motherboard.

22. The structure of claim 19 further comprising a via structure adjacent to at least one of the first and second conductive wire structures, wherein the via structure comprises substantially the same material as the first and second conductive wire structures.

23. The structure of claim 18 further comprising wherein at least one of the first and second conductive wire structures comprises at least one of copper, silver, tin and gold.

24. A structure comprising:

a first conductive wire structure disposed in a build up material, wherein the build up material comprises a portion of a package substrate; and

a second conductive wire structure disposed adjacent to the first interconnect structure, wherein a spacing between the first and second conductive wire structures comprises less than about 10 microns.

25. The structure of claim 24 further comprising a system comprising:

the first and second conductive wire structure;

a bus communicatively coupled to the first and second conductive wire structure; and

a DRAM communicatively coupled to the bus.

What is claimed is:

1. A method comprising:

forming at least one opening through a build up structure and a photo sensitive material disposed on the build up structure, wherein the build up structure comprises a portion of a package substrate;

filling the at least one opening with a metal containing nanopaste;

sintering the metal containing nanopaste to form a bulk property metal structure in the at least one opening; and

removing said photo sensitive material after sintering the metal containing nanopasts.

2. The method of claim 1 wherein the at least one opening comprises at least one fine conductive line opening comprising a width of less than 10 microns and a space between adjacent fine conductive line openings of less than 10 microns.

3. The method of claim 1 wherein the at least one opening comprises at least one via contact opening.

4. The method of claim 1 wherein the at least one opening is formed by utilizing at least one of nano imprinting and laser ablation.

5. The method of claim 1 wherein the bulk property metal structure comprises at least one of a metal contact via structure and a metal wire structure.

6. The method of claim 1 wherein a sintering temperature comprises less than 280 degrees Celsius for less than 60 minutes.

7. A method comprising:

forming at least one opening through a photo sensitive material and a build up structure, wherein the photosensitive material is disposed on the build up structure, and wherein the build up structure comprises a portion of a package substrate, and wherein the at least one opening comprises a width of less than 10 microns and a space of less than 10 microns between adjacent openings;

filling the at least one opening with a metal containing nanopaste; and

sintering the metal containing nanopaste to form a bulk property metal structure in the at least one opening.

8. The method of claim 7 wherein the package substrate comprises at least one of a high density package substrate and a motherboard.

9. The method of claim 7 wherein the metal containing nanopaste comprises nano-sized metal particles, dispersants, reaction rate control agents, and additives.

10. The method of claim 9 wherein the metal containing nanopaste comprises copper nanoparticles comprising a diameter of 6 nm or less, and wherein the dispersants comprise at least one of alkanoic acid and amine compounds, and wherein the reaction rate control agents comprise an amine compound, and wherein the additives comprise solvents.

11. The method of claim 7 wherein a sintering temperature comprises less than 280 degrees Celsius for 60 minutes or less.

12. The method of claim 11 wherein the sintering temperature of the metal containing nanopaste comprises a lower temperature than a melting temperature of the bulk property metal structure.

13. The method of claim 9 wherein the sintering removes the dispersants, reaction rate control agents, and additives from the metal containing nanopaste, and wherein the metal nanoparticles are transformed into a bulk property metal structure.

14. The method of claim 7 wherein filling the at least one opening with a metal containing nanopaste comprises at least one of squeezing and screen printing.

15. The method of claim 7 wherein a hydrophobic material is applied to the photosensitive material prior to filling the at least one opening.

16. The method of claim 7 wherein the at least one opening is formed with laser ablation.

17. The method of claim 7 wherein the bulk property metal structure comprises a metal wire structure with a line with of 10 microns or less and a line spacing of 10 microns or less.

18. A structure comprising:

a first conductive wire structure disposed in a build up material, wherein the build up material comprises a portion of a package substrate;

a second conductive wire structure disposed adjacent to the first conductive wire structure, wherein the first and second conductive wire structures comprise a width of less than 10 microns and a spacing between the first and second conductive wire structures of less than 10 microns.

19. The structure of claim 18 wherein the first and second conductive wire structures comprise a metal comprising bulk metal properties.

20. The structure of claim 18 wherein the first and second conductive wire structures comprise a metallic wire structure.

21. The structure of claim 18 wherein the package substrate comprises at least one of a high density package substrate and a motherboard.

22. The structure of claim 19 further comprising a via structure adjacent to at least one of the first and second conductive wire structures, wherein the via structure comprises the same material as the first and second conductive wire structures.

23. The structure of claim 18 wherein at least one of the first and second conductive wire structures comprises at least one of copper, silver, tin and gold.

24. A structure comprising:

a first conductive wire structure disposed in a build up material, wherein the build up material comprises a portion of a package substrate; and

a second conductive wire structure disposed adjacent to the first conductive wire structure, wherein a spacing between the first and second conductive wire structures comprises less than 10 microns.

25. The structure of claim 24 further comprising a system comprising:

the first and second conductive wire structure;

a bus communicatively coupled to the first and second conductive wire structure; and

a DRAM communicatively coupled to the bus.